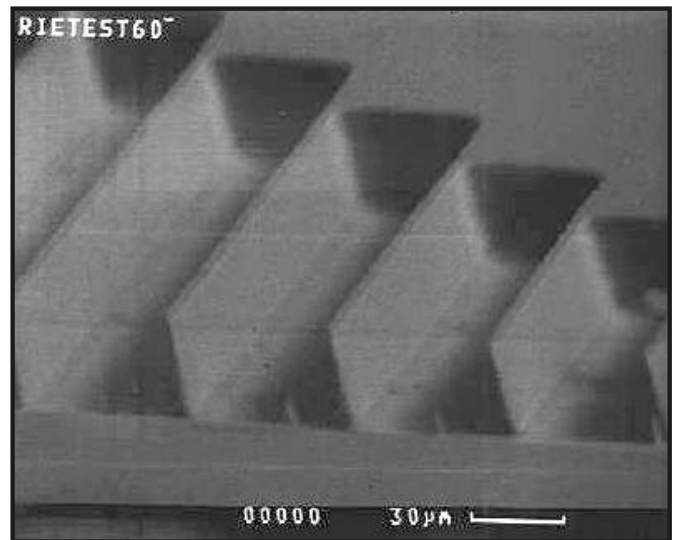
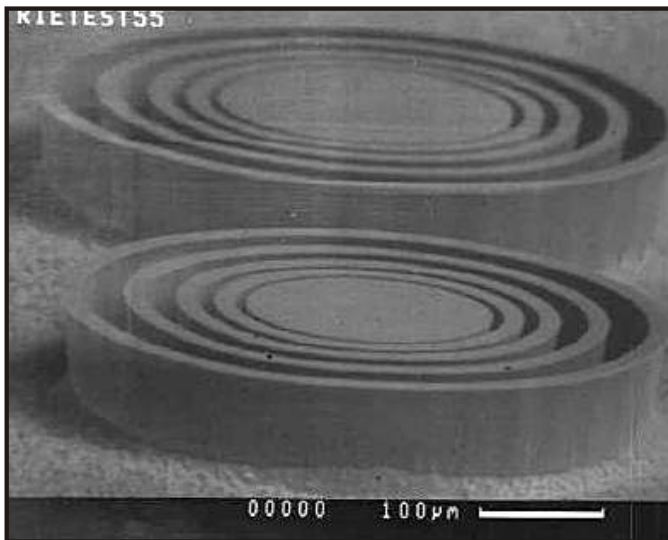


Plasmalab Data

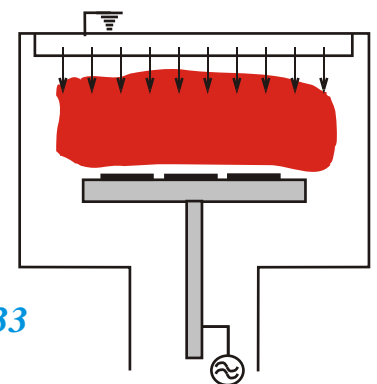
50 μm deep, anisotropic Si RIE for MEMS



50 μm deep etch in bulk Silicon
(Courtesy of Kevin Gaughan at Sarcos Research Corporation)



Plasmalab 80 Plus
Plasmalab System 100/ 133



Technology:

- Reactive Ion Etching (RIE)
- 13.56 MHz Plasma Excitation
- Fluorine based Process
- wide temperature range substrate electrode

Results:

- Rate : ca. 1.2 μm / min
- Mask: SiO_2
- Profile: anisotropic
- Uniformity (4"): +/- 2 %